

V_{DSS}	-12V
$R_{DS(on)}$ (Max.)	30mΩ
I_D	-4.5A
P_D	1.25W

●Features

- 1) Low on - resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSST8).
- 4) Pb-free lead plating ; RoHS compliant

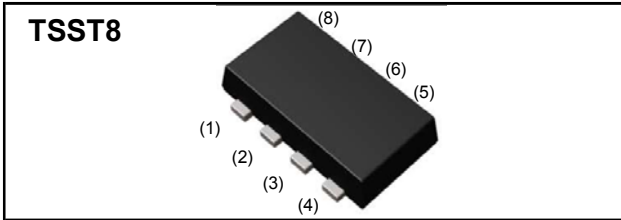
●Application

DC/DC converters

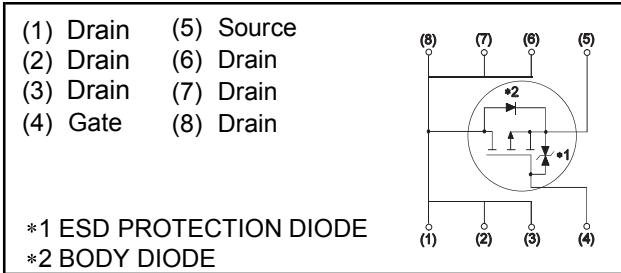
●Absolute maximum ratings($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	-12	V
Continuous drain current	I_D^{*1}	±4.5	A
Pulsed drain current	$I_{D,pulse}^{*2}$	±18	A
Gate - Source voltage	V_{GSS}	0 to -8	V
Power dissipation	P_D^{*3}	1.25	W
	P_D^{*4}	0.65	W
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3,000
	Taping code	TR
	Marking	SC

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA}^{*3}	-	-	100	°C/W
Thermal resistance, junction - ambient	R_{thJA}^{*4}	-	-	192	°C/W

●Electrical characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -1mA$	-12	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = -1mA$ referenced to 25°C	-	-12	-	mV/°C
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -12V, V_{GS} = 0V$	-	-	-10	μA
Gate - Source leakage current	I_{GSS}	$V_{GS} = -8V, V_{DS} = 0V$	-	-	-10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = -6V, I_D = -1mA$	-0.3	-	-1.0	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)th}}{\Delta T_j}$	$I_D = -1mA$ referenced to 25°C	-	2.6	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS} = -4.5V, I_D = -4.5A$	-	22	30	m Ω
		$V_{GS} = -2.5V, I_D = -2.2A$	-	28	39	
		$V_{GS} = -1.8V, I_D = -2.2A$	-	38	57	
		$V_{GS} = -1.5V, I_D = 0.9A$	-	50	100	
		$V_{GS} = -4.5V, I_D = -4.5A, T_j = 125^\circ\text{C}$	-	34	48	
Gate input resistance	R_G	$f = 1\text{MHz}, \text{open drain}$	-	20	-	Ω
Transconductance	g_{fs}^{*5}	$V_{DS} = -6V, I_D = -4.5A$	5.5	11	-	S

*1 Limited only by maximum temperature allowed.

*2 $P_w \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 Mounted on a ceramic board (30×30×0.8mm)

*4 Mounted on a FR4(20×20×0.8mm)

*5 Pulsed

●Electrical characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	4200	-	pF
Output capacitance	C_{oss}	$V_{DS} = -6V$	-	350	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	330	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx -6V, V_{GS} = -4.5V$	-	16	-	ns
Rise time	t_r^{*5}	$I_D = -2.2A$	-	60	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_L = 2.7\Omega$	-	400	-	
Fall time	t_f^{*5}	$R_G = 10\Omega$	-	150	-	

●Gate Charge characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*5}	$V_{DD} \approx -6V, I_D = -4.5A$ $V_{GS} = -4.5V$	-	40	-	nC
Gate - Source charge	Q_{gs}^{*5}	$V_{DD} \approx -6V, I_D = -4.5A$	-	6.5	-	
Gate - Drain charge	Q_{gd}^{*5}	$V_{GS} = -4.5V$	-	6.0	-	

●Body diode electrical characteristics (Source-Drain)($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_s^{*1}	$T_a = 25^\circ\text{C}$	-	-	-1	A
Forward voltage	V_{SD}^{*5}	$V_{GS} = 0V, I_s = -4.5A$	-	-	-1.2	V

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

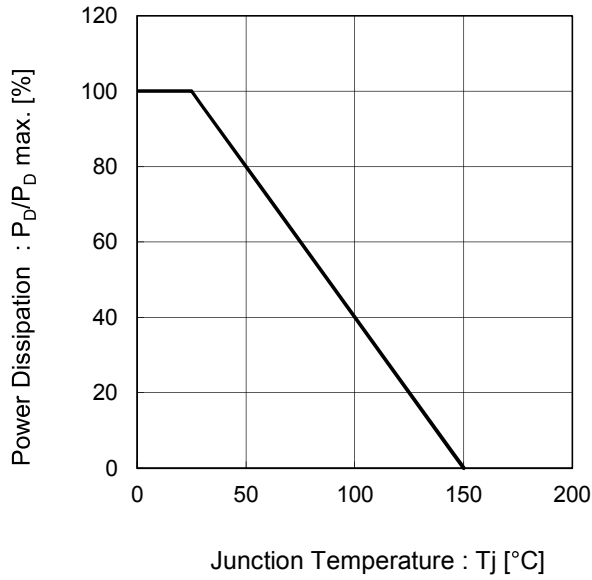


Fig.2 Maximum Safe Operating Area

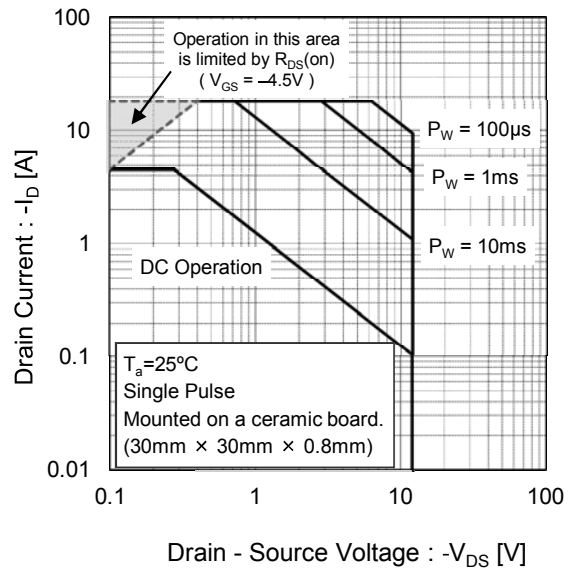


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

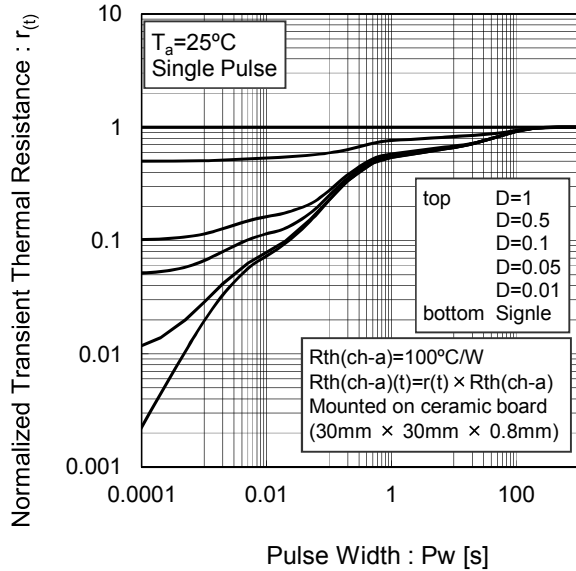
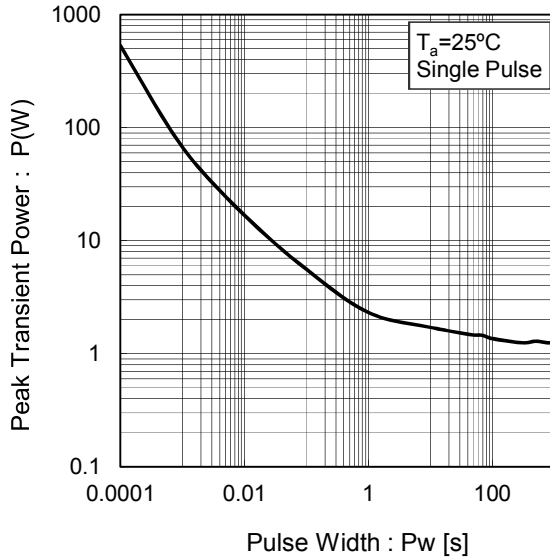


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

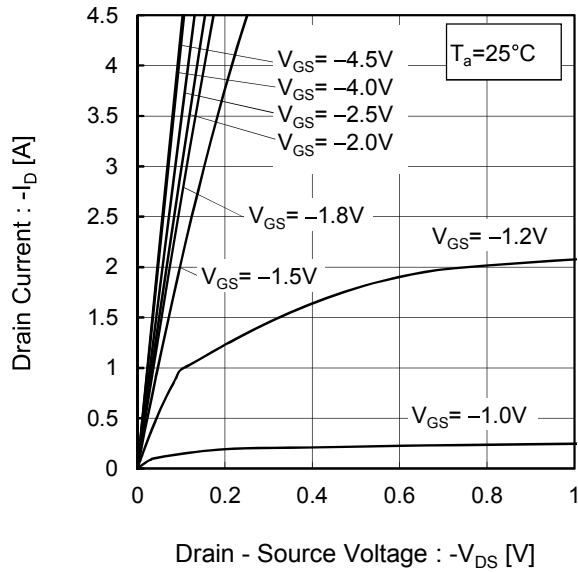
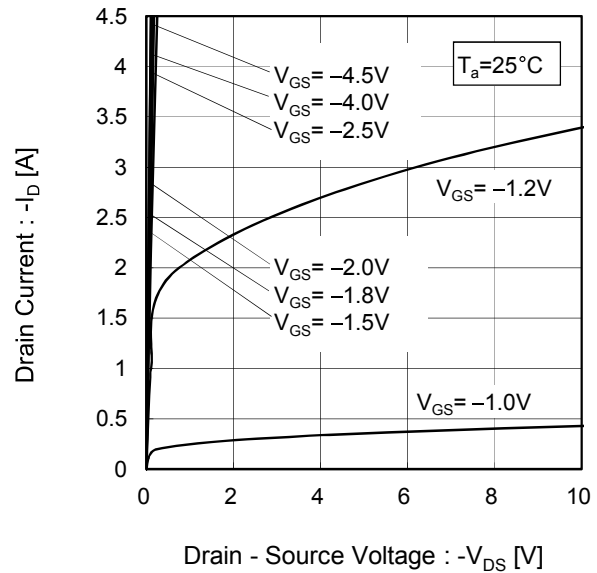


Fig.6 Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.7 Breakdown Voltage vs. Junction Temperature

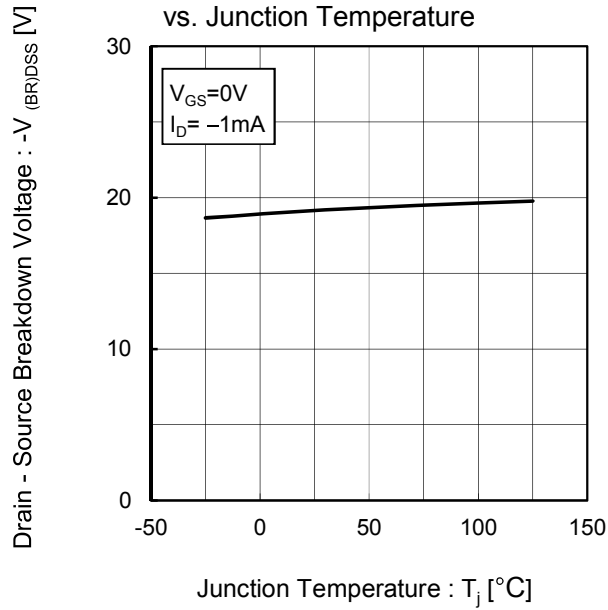


Fig.8 Typical Transfer Characteristics

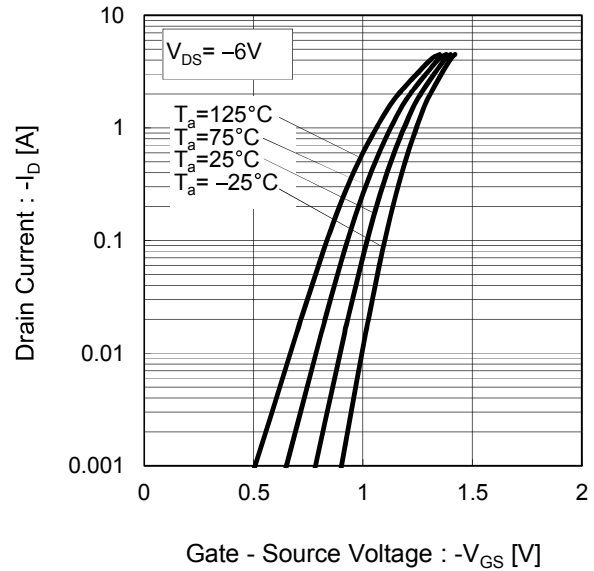


Fig.9 Gate Threshold Voltage vs. Junction Temperature

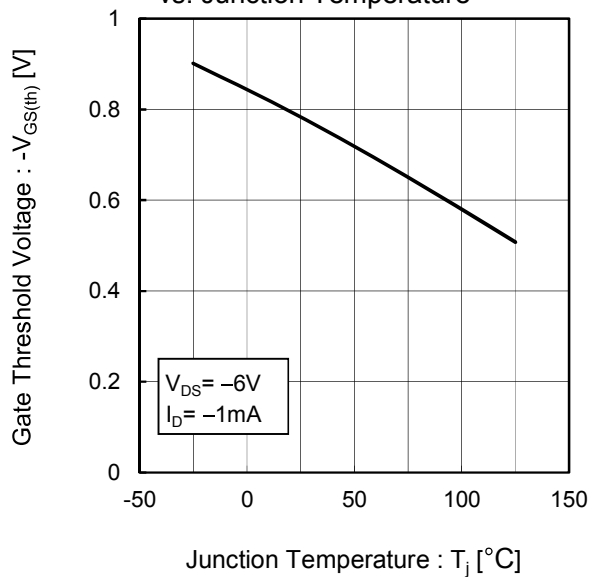
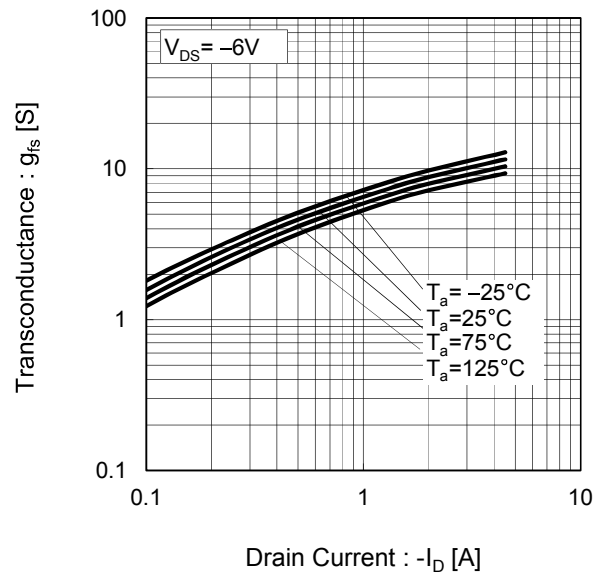


Fig.10 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.11 Drain Current Derating Curve

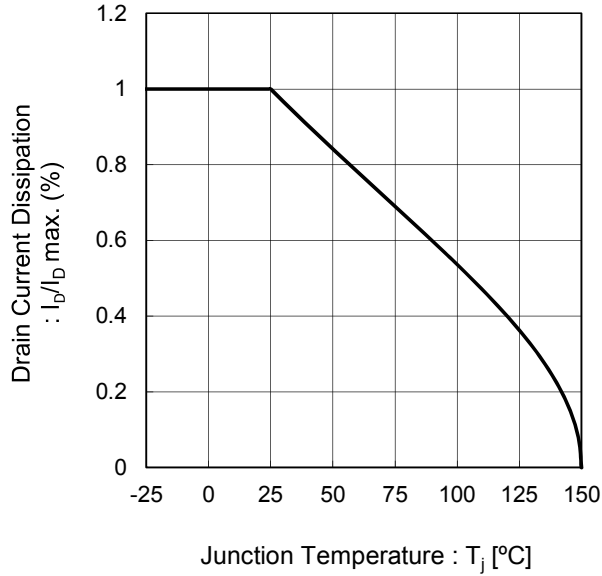


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

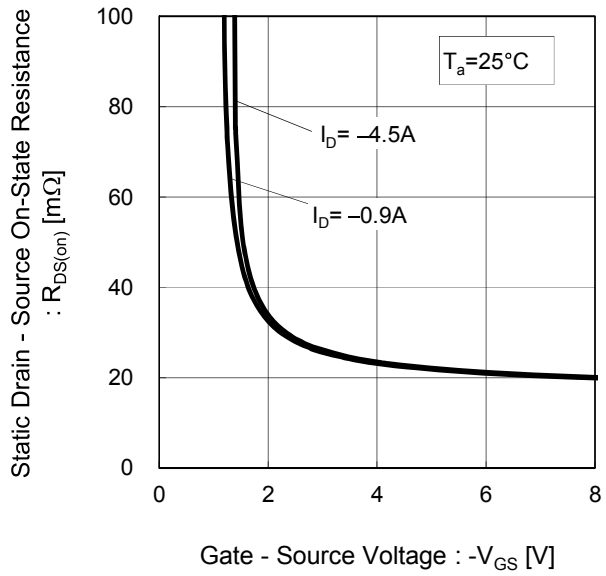


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)

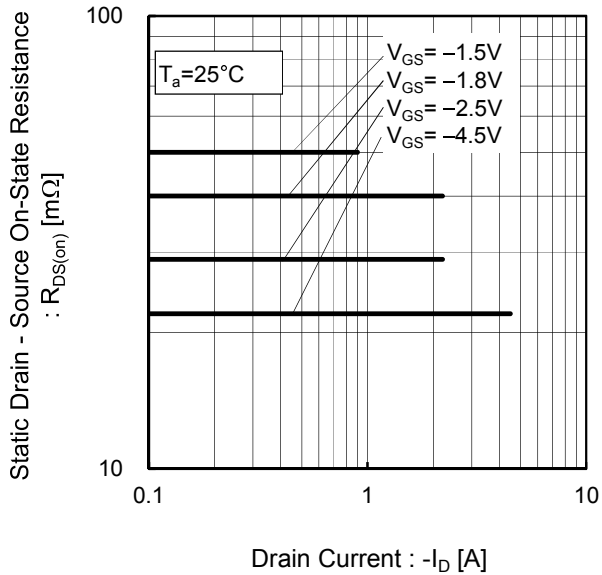
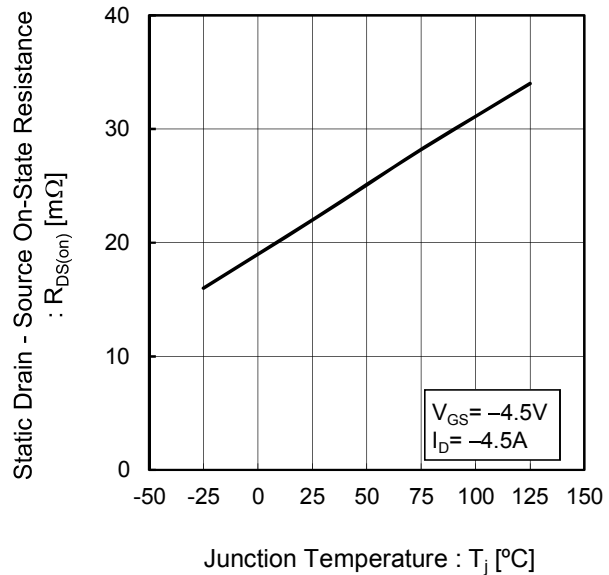


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



●Electrical characteristic curves

Fig.15 Static Drain-Source On-State Resistance vs. Drain Current(II)

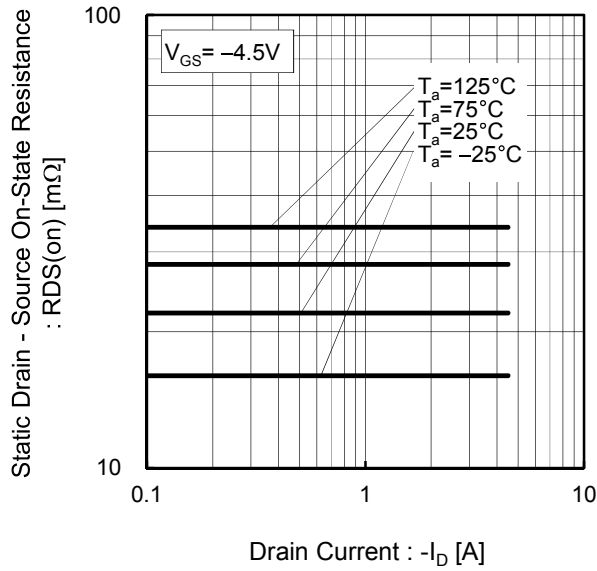


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)

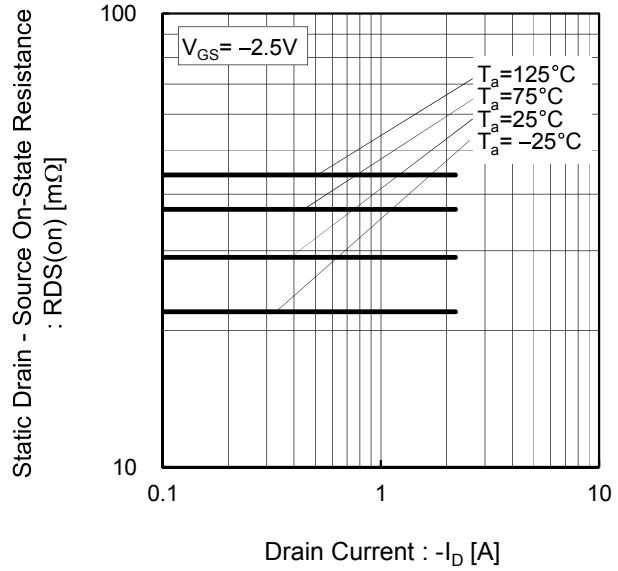
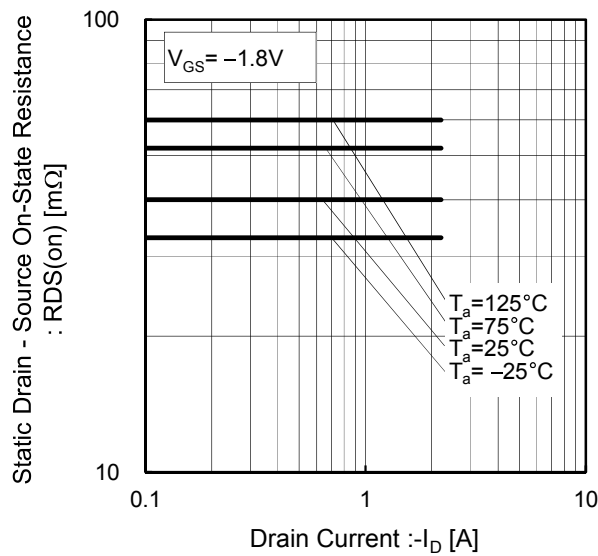


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)



● Electrical characteristic curves

Fig.18 Typical Capacitance vs. Drain - Source Voltage

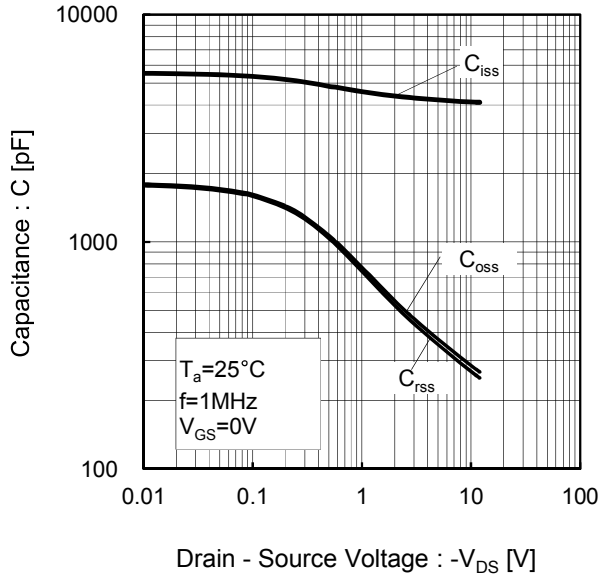


Fig.19 Switching Characteristics

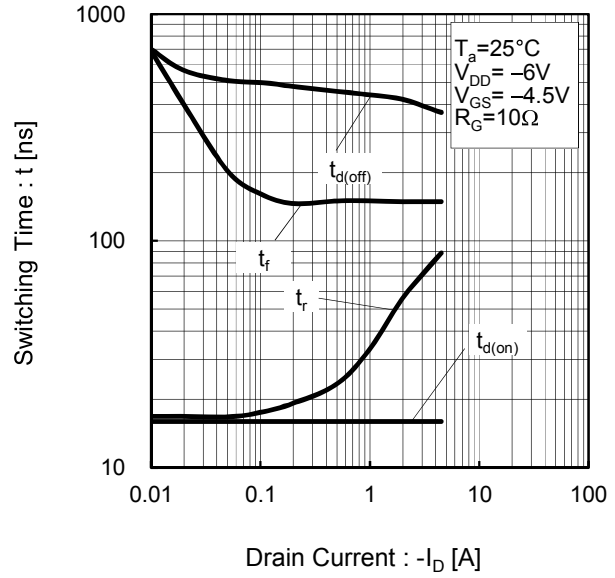


Fig.20 Dynamic Input Characteristics

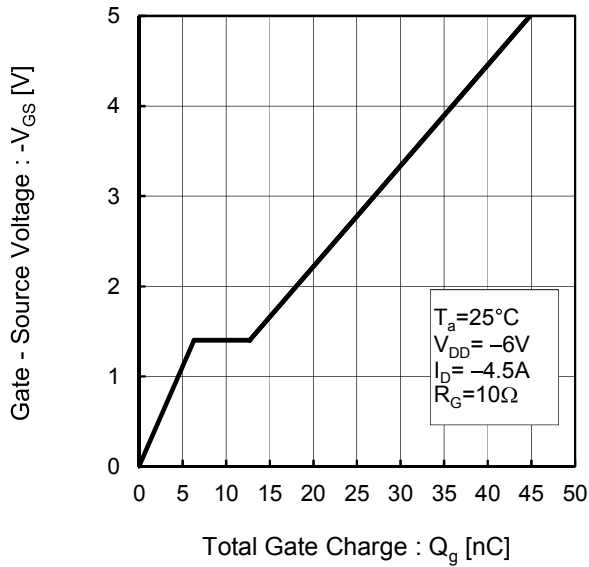
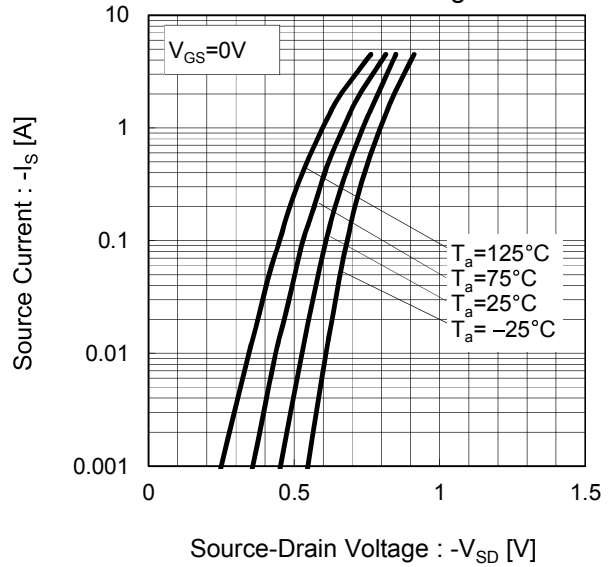


Fig.21 Source Current vs. Source Drain Voltage



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

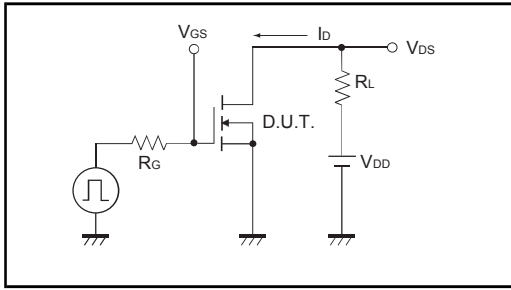


Fig.1-2 Switching Waveforms

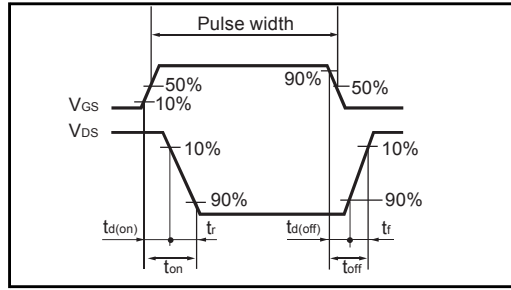


Fig.2-1 Gate Charge Measurement Circuit

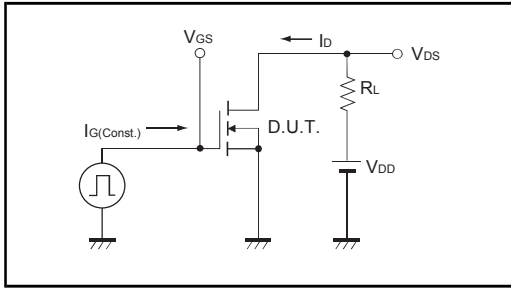
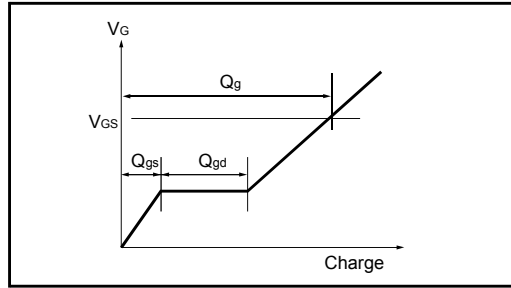
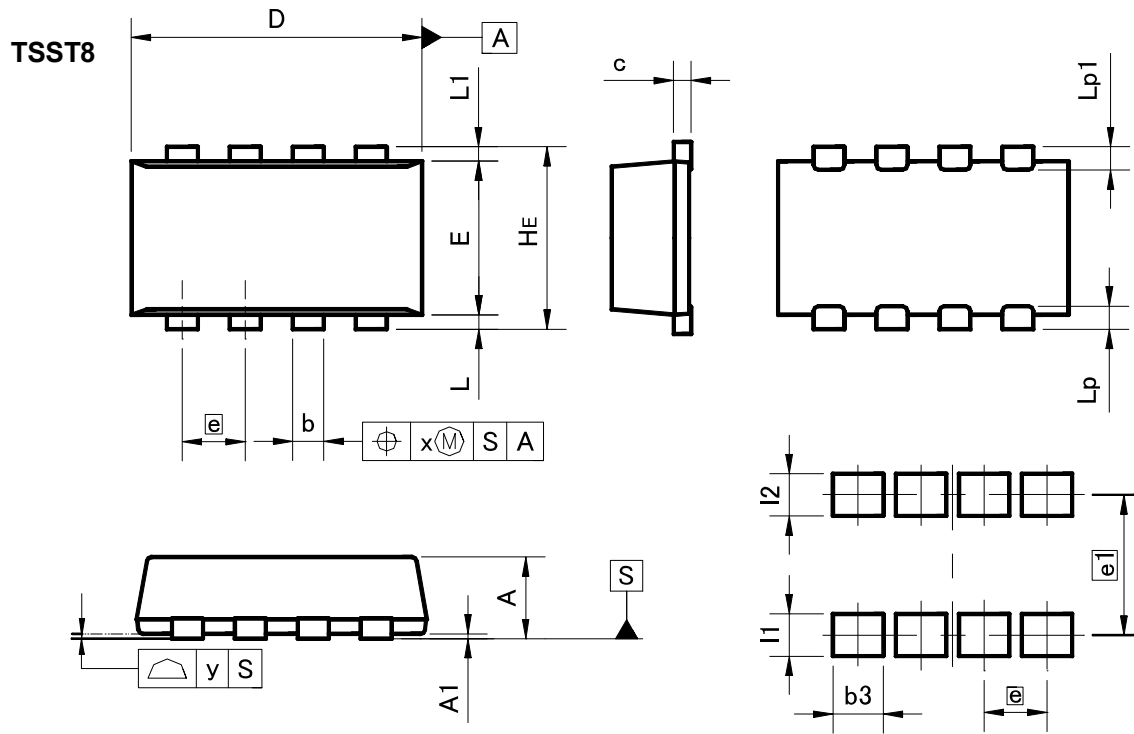


Fig.2-2 Gate Charge Waveform



●Dimensions (Unit : mm)



Pattern of terminal position areas

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.75	0.85	0.03	0.033
A1	0.00	0.05	0	0.002
b	0.22	0.42	0.009	0.017
c	0.12	0.22	0.005	0.009
D	2.90	3.10	0.114	0.122
E	1.50	1.70	0.059	0.067
e	0.65		0.03	
HE	1.80	2.00	0.071	0.079
L	0.05	0.25	0.002	0.01
L1	0.05	0.25	0.002	0.01
Lp	0.15	0.34	0.006	0.013
Lp1	0.15	0.34	0.006	0.013
x	-	0.10	-	0.004
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
e1	1.46		0.06	
b3	-	0.52	-	0.02
I1	-	0.44	-	0.017
I2	-	0.44	-	0.017

Dimension in mm/inches

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RT1A045AP - Web Page

[Distribution Inventory](#)

Part Number	RT1A045AP
Package	TSST8
Unit Quantity	3000
Minimum Package Quantity	3000
Packing Type	Taping
Constitution Materials List	inquiry
RoHS	Yes